# Development of Uniform CdTe Pixel Detectors Based on Caltech ASIC

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## ABSTRACT

We have developed a large C dTe pixel detector with dimensions of 23.7  $13.0 \text{ mm}^2$  and a pixel size of 448 448 m<sup>2</sup>. The detector is based on recent technologies of an uniform C dTe single crystal, a two-dimensional A SIC, and stud bum p-bonding to connect pixel electrodes on the C dTe surface to the A SIC. G ood spectra are obtained from 1051 pixels out of total 1056 pixels. When we operate the detector at {50 C, the energy resolution is 0.67 keV and 0.99 keV at 14 keV and 60 keV, respectively. Week-long stability of the detector is con med at operating tem peratures of both {50 C and {20 C. The detector also shows high uniform ity: the peak positions for all pixels agree to within 0.82 %, and the average of the energy resolution is 1.04 keV at a tem perature of {50 C. When we norm alized the peak area by the total counts detected by each pixel, a variation of 2.1 % is obtained.

K eyw ords: CdTe, CZT, uniform ity, hard X-ray detector, pixel detector, stud bum p bonding, in aging spectrom eter

# 1. IN TRODUCTION

O ne of the prim ary elds of high energy astro-physics in the near future is the hard X-ray universe, where nontherm all processes such as particle acceleration and nucleo-systhesis become dom inant. The combination of the two new technologies of hard X-ray focusing m into optics<sup>1</sup> and hard X-ray in aging spectrom eters<sup>2</sup> at the focal plane w ill provide two orders of magnitude in provement in both detection sensitivity and in aging resolution.<sup>3(5</sup> For example, the N eX T m ission<sup>3,6</sup> proposed in Japan has m intors with a focal length of 12 m and an angular resolution up to 15 arcsec.<sup>7</sup> The detector is required to have an energy coverage from 5 keV to 80 keV, with an energy resolution better than 1.0 keV (FW HM) for 60 keV line -rays.<sup>8</sup> An aperture size of 20{30 m m in diam eter with a spacial resolution of 200 { 250 m is needed to take advantage of the perform ance of the m intor. The detector should have a good tim ing resolution in the range 10 { 100 s on an event by event basis to reduce the intrinsic background in the detector by the anti-coincidence technique. G ood uniform ity in both the detection e ciency and the spectroscopic properties is necessary not only to obtain high quality im age and spectra, but also to perform proper background subtraction.

C adm ium telluride (C dTe) and cadm ium zinc telluride (C ZT) are promising devices as the focal plane detector since they have a high detection e ciency comparable to N aI scintilators, a good energy resolution comparable to G e detectors, and can be operated at room temperature. Thanks to signi cant progress on technologies of crystal growth, large area detectors based on C dTe and C ZT are now available. Recently, H arrison et al. has developed a large area C ZT pixel detector with a new ly developed low-noise A SIC for the front end.<sup>9</sup> The detector shows a good energy resolution of < 1 keV. How ever, the present high pressure B ridgem an m ethod, which is offen used to grow C ZT crystal, only yields polycrystals and therefore the yield of obtaining large (> 1

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cm<sup>2</sup>) and uniform portions of single CZT crystals is low. To control the mobility and carrier lifetim e within the whole wafer seems to be di cult.<sup>10,11</sup> This non-uniform ity is the issue of the current CZT pixel detectors. On the other hand, CdTe crystal grown by the Traveling Heater M ethod (THM -CdTe) can provide a single crystal as large as 40 mm 40 mm.<sup>12</sup> Based on the THM -CdTe wafers, we have been working on high perform ance CdTe detectors for both planar and pixel con guration.<sup>13</sup>(16)

In order to improve the current hard X -ray imaging detector by utilizing the recent C dTe technology, we have developed a pixel detector under the collaboration of ISA S and C altech. In this collaboration, a two-dimensional large area analog A SIC and the read out system is prepared by C altech. A large size C dTe crystal with pixel electrodes and the bump bonding technologies are prepared by ISA S. In this paper, uniform ity of the pixel detector as well as basic perform ance of the C dTe pixel detector is presented.

## 2.CDTE PIXEL DETECTOR

The uniform charge transport properties of the wafer are very in portant for fabricating large area pixel detectors. The C dTe crystalused here is the THM -C dTe m anufactured by A C R O R A D  $^{12}$  A n electrical resistivity of 1 10<sup>9</sup>

cm (p-type) is achieved by compensating the native defects with Cl. The grown crystal is large enough to obtain (111) oriented single crystal wafers with an area as large as  $25 \quad 25 \text{ mm}^2$ . We have demonstrated that the wafer shows very good uniform ity when we make a large area CdTe detector with planar electrodes.<sup>13,14</sup> As determined by the measurements with a large planar detector (21  $21 \text{ mm}^2$ ) by using a collimated -ray beam from an <sup>241</sup>Am source, the location of the peak in the pulse height distribution agrees to within 0.1 % and the variation of the area of the 60 keV peak is less than 0.9 %, regardless of the position.

A schem atic drawing of the detector is shown in Fig. 2. The detector consists of a CdTe wafer, a frontend ASIC and the data handling circuit including an ADC and a CPU. Charge signals from the individual pixel electrode are fed into the readout circuit built in the ASIC. The ASIC is originally developed by the Caltech group for a CZT pixel detector and features very low noise by means of a capacitor array.<sup>17</sup> The power consumption of the ASIC is as low as 50 W /pixel.

Before assembling the detector, a CdTe wafer with dimensions of 23.7  $13.0 \text{ mm}^2$  and a thickness of 0.5 mm is prepared. By using polished wafers with (1 1 1) orientation, Pt electrodes are formed by electroless plating for both the common electrode (cathode) and pixel electrodes (anode). The size of each pixel electrode is 448 m 448 m with a gap of 52 m. No control electrode is adopted between electrodes. A guard with 1 mm width surrounds the 24 44 pixels anode pixels.



Figure 1. Photo of the pixel detector. The detector has dimensions of 23.7  $13.0 \text{ mm}^2$  and a thickness of 0.5 mm. The cathode surface is shown in the picture. The bias voltage is supplied from the top board to the cathode.



F igure 2. Schem atic drawing. The detector consists of CdTe, ASIC, stud bumps between them, an o -chip ADC, and a microprocessor for the readout logic.



F igure 3. (a) Schem atic diagram of the the circuit for one pixel which is in plem ented in the ASIC, and (b) An example of an output waveform. The circuit has a charge ampli er, a shaping ampli er, a discrim inator, and a capacitor array of 16 capacitors. The outputs are sixteen samplings by the array of capacitors.

O ne of the most di cult parts to realize a ne pitch ( ner than several hundred m icrons) C dTe and/or C ZT pixel detectors is to establish a simple and robust connection technology for these fragile devices. High compression and/or high am bient temperature would dam age the crystal. A loo the co-planarity of the C dTe wafer is measured to be 2 m at most, which is much worse than that of usual silicon wafers. U sual indium -ball soldering m ight not be appropriate for this purpose. A loo indium is easily oxidizable, and needs ux which could contam inate the detector surface. Recently, we have developed indium and gold (In/Au) stud-bump bonding technology, optim ized for C dTe detectors, with M itsubishi H eavy Industries (M H I) in Japan. By following the prescription given in Takahashi et al.<sup>18</sup> but with a slightly modi ed bump condition, we connected the C dTe wafer to the A SIC. In order to m inim ize the e ect of incom plete charge collection, we apply a negative bias on the comm on electrode. A fler we assembled the detector, we have con im ed the connection of 1055 pixels out of 1056 pixels. There is one bad pixel which shows very high noise, regardless of any conditions, such as bias voltage, and tem perature. C urrently, we do not understand whether the read out circuit is broken, or the bum p is not connected for this particular pixel.

In the ASIC (Fig. 3 (a)), output signal from the pream pli er is continuously integrated by one capacitor to the next with a time interval of 1 s. A fler a trigger signal is issued from a comparator, the switching sequence continues for the next eight capacitors and then the sequence is freezed for the subsequent readout. The charge in sixteen capacitors is sequentially read out as voltage and converted by the external ADC. Figure 3 (b) shows an example of the output signal for one pixel. Pulse height inform ation for each X-ray photon is calculated by analyzing the recorded pulse shape by the liter algorithm in plemented in DSP or by software. The ASIC also reads out data from the surrounding eight pixels together with the data from the triggered pixel. A detailed description of the ASIC is given in Chen et al.<sup>17</sup> For the detector used in this experiment, triggers from ve pixels are turned o , because these channels show rather high noise as compared to other channels. The typical noise level is about 50 ADC channel for norm al pixels, while the noise level of bad channels is larger than 200 ADC channel. From hereafter, we analyze spectra from 1051 pixels out of total 1056 pixels. At 20 C, the FW HM of the peak measured by the test pulse ranges from 0.4 keV to 0.6 keV when the bias voltage is not applied. This corresponds to the electronic noise of 40 { 60 e (RM S).

The spectrum from each pixel is constructed from the pulse height inform ation associated with the triggered There are two types of events; 1) single-pixel events in which the pulse height of pixels surrounding the triggered pixel is comparable with the noise level, and 2) multi-pixel events in which the energy deposited in the CdTe detector is shared with multiple pixels.

#### 3.SIGNAL PROCESSING AND SPECTRAL ANALYSIS

In order to study the spectral perform ance of the C dTe pixel detector, we start from the search for the optim um operating condition and the investigation of the response from a single pixel. The overall perform ance, including the pixel by pixel variation will be discussed in the next section.

As the st demonstration of the operation of the CdTe pixel detector, Fig. 4 show  $s^{241}$ Am spectra taken at 20 C and 50 C.Single-pixel events are used to make the spectra. Energy resolutions better than 1 keV (FW HM) are obtained for -ray lines from 14 keV to 60 keV in the spectra. The best resolution is obtained when the detector is operated at the low est tem perature, 50 C.W ith a bias voltage of 100V, the energy resolution at 14 keV and 60 keV is 0.67 keV and 0.89 keV, respectively. The in provement in the spectral resolution is due to the reduction of the leakage current. At 20 C, the leakage current is estim ated to be an order of 10 pA per pixel at {100 V, which is calculated from the results obtained with a planar detector with Pt/CdTe/Pt electrode con guration. A lthough we need to perform more quantitative measurements, the leakage current at {50 C is expected to be reduced by alm ost an order of magnitude as com pared to that at {20 C.

Charge collection e ciency (CCE) is an important issue for CdTe and CZT, because electrons and holes generated in these sem iconductor have low mobility and a short life-tim e.<sup>19</sup> The low CCE results in the tail-like structure below the peak in the spectrum, which is actually seen in the <sup>241</sup>Am spectra (Fig. 4). We study the CCE quantitatively by measuring the <sup>57</sup>Co spectrum at dimensional transmission of the spectrum of the case of the 40 V operation (Fig. 5), a signing cantile amount of charge loss is seen as a low-energy tail of the 122 keV line. As the bias voltage is increased to 300 V, a sharp 122 keV peak is obtained. A higher bias voltage is better in terms of the CCE because the fraction of electrons and holes that reach the electrodes increases. However, high bias voltage deteriorates the spectral resolution due to the increase of the lakage current. In the measurements, the best energy resolution for the 14 keV line is obtained at 40V. On the other hand, the best energy resolution of 1.47 keV for the 122 keV line is obtained at 300 V. This is because most of the 14 keV photons interact close to the cathode electrodes, and because the transit of electrons, which is less a low charge loss, become se responsible for the pulse height. As an optimum value, we use 300 V as the standard bias voltage from here after.

Since the pixel size is as small as 500 m for the CdTe pixel detector, we need to investigate the charge splitting among the adjacent pixels (multi-pixel event). Figure 6 shows a correlation of pulse heights between a triggering pixel and one of the adjacent pixels. It is shown that the energy deposition, corresponds to the 122 keV -ray, is shared between two pixels, for some fraction. Figure 7 com pares spectra for single-pixel and multi-pixel events. It is clearly shown that the amount of the tail component is more pronounced when we include multi-pixel events. This im plies that the selection of single-pixel events is important to obtain \tail-less" spectra in the CdTe pixel detector.



Figure 4.<sup>241</sup>Am spectra obtained at  $\{20 \text{ C and } \{50 \text{ C.}^{241}\text{Am} \text{ illum inates the detector from 40 cm} above the cathode plane of the detector.$ 



Figure 5.  $^{57}$ Co spectrum obtained at an operating temperature of {50 C with di erent bias voltages. The applied bias is 40 V, 100 V, and 300 V. All the spectra are drawn by using single-pixel events in which no signal larger than 5 keV is detected in the surrounding pixels. The energy resolution for the 14 keV line is as low as 0.61 keV at the bias voltage of 40V. The size of the low energy tail is reduced as the bias voltage increases.



Co-57 100V, -50°C single-pixel events 1000 multi--pixel events incl. abo 500 Counts 100 50 10 5 1 0 25 50 75 100 125 150 Energy [keV]

F igure 6. Correlation between pulse height (ADC channel) from a triggering pixel and that of the adjacent pixel. The horizontal axis is the ADC channel for the triggered pixel while the vertical axis for the adjacent pixel.

F igure 7. Spectra both for single-pixel events (black) and multi-pixel events including single-pixel events (dash). A low energy threshold of 5 keV is used to discrim inate hits in the surrounding pixels.

Long-term stability is an important issue for C dTe and C ZT sem iconductors.<sup>18</sup> A s discussed in our previous publication,<sup>13</sup> a C dTe detector with Pt electrode for both cathode and anode sides (Pt/C dTe/Pt) shows good stability. We do not see any spectral degradation for a long term operation of a week or more. In order to verify this with the C dTe pixel detector, we operate it for seven days at an operating tem perature of  $\{50 \ C \ under a \ bias of 300 \ V \ An \ ^{241} Am \ source is placed above the detector during the measurem ent. Figure 8 shows the spectra taken at the rst day, 1 day later, and 7 days later. No degradation can be observed in the peak positions and the energy resolution. The location of the peak in the pulse height distribution agrees to within 0.2% . The energy resolutions (FW HM) agree within statistical errors. The detector also shows a stable spectral perform ance at <math>\{20 \ C \ over one week$ .



Figure 8. Spectra taken at the st day, 1 day later, and a week later after the bias voltage is applied. An operating temperature is {50 C and a bias voltage is 300 V. The spectra are drawn by sum ming 10 pixels.

#### 4.UN IFORM ITY OF THE DETECTOR

Evaluating the detector uniform ity response is an important objective of this experiment. We analyze the uniform ity of the detector in terms of spectral properties such as the peak position and the spectral resolution, as well as the detection e ciency.

The location of the peak in the spectrum for mono-energetic -rays has a strong correlation with the charge transport properties of the material,  $^{10,19}$  especially for electrons. If the mobility-lifetime product is not uniform in the wafer used in the detector, the peak position changes with the pixel location, since we apply a single bias voltage over the entire detector plane. The variations of the size of low energy tail is explained if the transport properties for holes have some spatial distribution. These spatial variations of charge transport properties could be introduced if the crystal is not uniform ly grow n.

We study the uniform ity by irradiating with an <sup>241</sup>Am source from 40 cm above the detector, and obtain at illumination data. The detector is operated under a bias of 300 V, at a temperature of 50 C. In order to evaluate the charge transport properties, the analog gains for each pixel are calibrated by the using the on-chip



F igure 9. M ap of the peak positions of the 60 keV line. The white spots at the right center and top left are disabled pixels.



F igure 10.D istribution of the 60 keV peak positions after the analog gain of the ASIC is calibrated by m eans of pulser data. The variation for the peak position is less than 0.82 %.



F igure 11. D istribution of the energy resolution (FW HM) for the 60 keV line. The mean and standard deviation of the distribution are 1.04 keV, and 0.10 keV.

test pulse. The average gain variation is 2.8 %, consistent with the number reported in Harrison et al.<sup>20</sup> Figure 9 shows the spatial distribution of the peak position in ADC channel after the gain of readout circuit in the ASIC is calibrated. Distribution of the peak position is almost at and shows a standard deviation of 0.82 % (Fig. 10), which agrees with the result from the scanning experiment of a planar CdTe detector.<sup>14,18</sup> D istribution of the standard deviation of 4.2 % (Fig. 11. The average energy resolution is 1.04 keV, and the standard deviation is 0.10 keV.

The variation of the count rate is also an important aspect for the pixel detector, since it releases the variations of the detection electron in the detector. In order to produce precise-spectroscopic images, the late ciency in the detector plane is desirable to reduce the system atic errors. The uniform ity of charge transport properties is again important here. This is because the pixel-to-pixel variation of the fraction of low energy tail a lects the atness of the image when we specify the energy band. D istribution of the area for the 60 keV peak is plotted in Fig. 12. The area is calculated by integrating counts from 45 keV to 65 keV. The variation of the distribution is 8.9 %, which is larger than the statistical variation of 1.1 %. This result is inconsistent with the result for the planar C dTe detector.<sup>14,18</sup>

In order to investigate the reason for the variation of the area, we com pare the counts in the 60 keV peak and the total count, and obtain a scatter plot (Fig. 13). From the gure, a strong correlation between the two values is observed. In Fig. 14, we com pared the actual spectra of the pixels with the highest and the lowest count at 60

total counts



60 keV peak counts

F igure 12.Count variation for the 60 keV peak. The variation is 8.9 % .

Figure 13. Correlation between 60 keV peak counts and total counts for each pixel.



Figure 14. Spectra for the two extrem es of the total counts.



F igure 15. M ap for the 60 keV peak area norm alized by the total counts detected by each pixel. The white spots are disabled pixels.



F igure 16.D istribution for the 60 keV peak area norm alized by the total counts. The variation of the distribution is 2.1 % .

keV. A lthough the counts are di erent, the shape of the spectra is very sim ilar. This sim ilarity im plies that the variation of the peak area or the total count rate is not caused by the spatial inhom ogeneity of charge transport properties, such as m obility and lifetime. This variation then could be explained by two possibilities. One is a reduction of the elective area caused by the bum p bonding process. The other is the dead time variations due to the algorithm currently installed in the data acquisition (DAQ) system. We will study this issue more.

If we assume that the variation of total counts is due to the dead-time variations for each pixel, we can use it as an indicator of the actual integration time for each pixel. Figure 15 shows a map of the \normalized" area (area ratio). In the gure, the integrated counts from 45 keV to 65 keV are normalized by the total counts of the spectrum for each pixel. The resultant variation of the area ratio is 2.1 % while the statistical error is 1.3 %.

## 5. IM AG ING SPECTROSCOPY

W e perform in aging m easurements to demonstrate the performance of in aging spectroscopy. An in age mask, made of brass covered with gold, is mounted 6 mm above the detector. It has a length of 70 mm and a thickness

of 0.8 mm. The area marked in Fig. 17 (a) is used for the measurement.  $^{241}$ Am and  $^{57}$ Co are located 40 cm above the detector so that the shadow in age is obtained with the CdTe pixel detector. The detector is operated at {20 C and 80 V for the pixel is applied.

As shown in Fig. 17 (b) and (c), we have succeeded in imaging spectroscopy using the detector. Fig. 17 (b) is drawn by 13 keV -26 keV lines from  $^{241}$ Am, while Fig. 17 (c) is by 122 keV line from  $^{57}$ Co. The spoke feature of the mask, which is the same as the pixel size of 500 m, is clearly resolved while a featureless image is obtained for the image selected from the 105 { 130 keV energy band. This result is consistent with the fact that the mask is transparent above 100 keV.



F igure 17. (a) Photo of a mask, and in ages using (b) 13 keV -26 keV lines of  $^{241}$ Am and (c) the 122 keV line of  $^{57}$ Co, respectively. The mask is made of brass covered with gold. A rectangular area is used in the measurement.

## 6.SUMMARY

We have developed a large C dTe pixel detector by utilizing recent technologies of an uniform C dTe single crystal, the two-dimensional A SIC, and the In/A u stud bump bonding. When the detector is operated at a temperature of {50 C, the energy resolution (FW HM) for the 14 keV and 60 keV —rays is 0.67 keV and 0.89 keV, respectively. The voltage scanning measurement shows that 10 % of the total event become multipixel events, which contributes to the tail structure in thespectra obtained. The detector shows high uniform ity as well as the spectral and im aging perform ances. The location of the peak agrees to within 0.82 % after the analog gain is calibrated by pulser data, and the average energy resolution is 1.04 keV. The variation of the 60 keV peak counts is found to be 8.9 %, which is inconsistent with the result for the planar C dTe detector. A lthough the reason for this variation is still under investigation, if we assume a \norm alized" area, the resultant variation is 2.1 %. In the dem onstration of im aging spectroscopy, the detector resolves a 0.5 mm wide line, which is the same as the positional resolution.

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